

140 COMMERCE DRIVE MONTGOMERYVILLE, PA 18936-1013 PHONE: (215) 631-9840 FAX: (215) 631-9855

RF AND MICROWAVE TRANSISTORS HF SSB APPLICATIONS Features DESIGNED FOR HIGH POWER PULSED IFF, DME, **TACAN APPLICATIONS** 80 W (typ.) IFF 1030 – 1090 MHz 75 W (min.) DME 1025 - 1150 MHz 50 W (typ.) TACAN 960 -1215 MHz 8.0 dB MIN. GAIN

- **REFRACTORY GOLD METALLIZATION**
- EMITTER BALLASTING AND LOW THERMAL **RESISTANCE FOR RELIABILITY AND RUGGEDNESS**
- **INFINITE LOAD VSWR CAPABILITY AT SPECIFIED OPERATING CONDITIONS**
- **INPUT MATCHED COMMON BASE CONFIGURATION**

DESCRIPTION:

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The MSC1075MP is a gold-metallized silicon. NPN power transistor designed for applications requiring high peak power and low duty cycles, such as IFF, DME, and TACAN. It is packaged in the .280" input-matched stripline flange package, resulting in improved broadband performance and low thermal resistance.

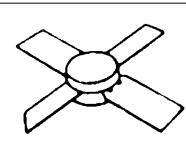


Symbol	Parameter	Value	Unit
V _{сво}	Collector-Base Voltage	65	V
V _{CES}	Collector-Emitter Voltage	65	V
V _{EBO}	Emitter-Base Voltage	3.5	V
Ιc	Device Current	5.5	Α
PDISS	Power Dissipation	218.7	W
ΤJ	Junction Temperature	+ 200	°C
Т _{stg}	Storage Temperature	-65 to +150	°C

THERMAL DATA

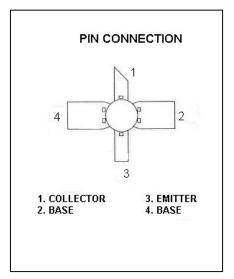
R _{TH(j-c)} Junction-Case Thermal Resistance	0.8	°C/W
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MSC1075MP

.280 4LSL (M115) hermetically sealed





MSC1075MP

ELECTRICAL SPECIFICATIONS (Tcase = 25°C)

STATIC

Symbol	Test Conditions		Value			
		Min.	Тур.	Max.	Units	
BV _{CBO}	I _c = 10 mA	I _E = 0 Ma	65			V
BV _{CES}	I _c = 25 mA	$V_{BE} = 0 V$	65			V
BVEBO	I _E = 10 mA	I _C = 0 mA	3.5			V
I _{CES}	V _{CE} = 50 V	l _E = 0 mA			5	mA
h _{FE}	$V_{CE} = 5 V$	$I_{C} = .1 A$	10			

DYNAMIC

Symbol	Test Conditions		Value		
Symbol	Test conditions	Min.	Тур.	Max.	Units
Pout	f = 1025 – 1150 MHz P _{IN} = 13.0 W V _{CE} = 50 V	75			W
G _₽	$f = 1025 - 1150 \text{ MHz}$ $P_{IN} = 13.0 \text{ W}$ $V_{CE} = 50 \text{ V}$	7.5			dB

Note: Pulse width = 10µSec. Duty Cycle = 1%

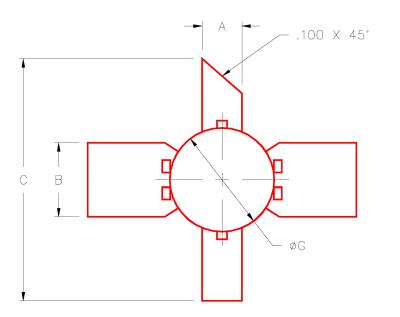
This device is suitable for use under other pulse width/duty cycle conditions. Please contact the factory for specific applications assistance.

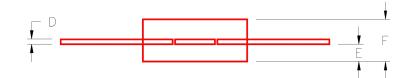


MSC1075MP

PACKAGE MECHANICAL DATA

PACKAGE STYLE M115





	MINIMUM	MAXIMUM	MINIMUM	MAXIMUM
	INCHES/MM	INCHES/MM	INCHES/MM	INCHES/MM
A	.095/2,41	.105/2,67		
В	.195/4,95	.205/5,21		
С	1.000/25,40			
D	.004/0,10	.007/0,18		
E	.050/1,27	.065/1,65		
F	.120/3,05	.135/3,43		
G	.275/6,99	.285/7,21		

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